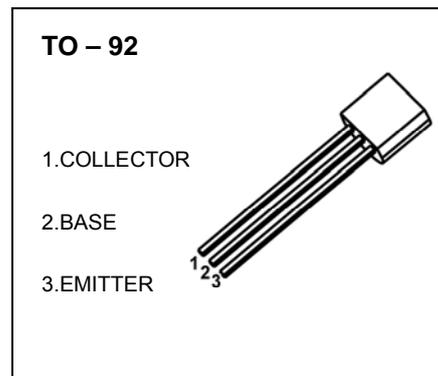


TO-92 Plastic-Encapsulate Transistors

BC516 TRANSISTOR (PNP)

FEATURES

- High DC Current Gain
- High Collector Current



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-10	V
I _C	Collector Current	-1	A
P _C	Collector Power Dissipation	625	mW
R _{θJA}	Thermal Resistance Junction To Ambient	200	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-40			V
Collector-emitter breakdown	V _{(BR)CEO}	I _C =-2mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-10			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-20mA	30000			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-0.1mA			-1	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-0.1mA			-1.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V, I _C =-10mA			-1.4	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz		200		MHz